



TO-92 Plastic-Encapsulate Transistors

BF421
BF423

TRANSISTOR (PNP)

FEATURES

Power dissipation

 P_{CM} : 0.83 W ($T_{amb}=25^{\circ}C$)

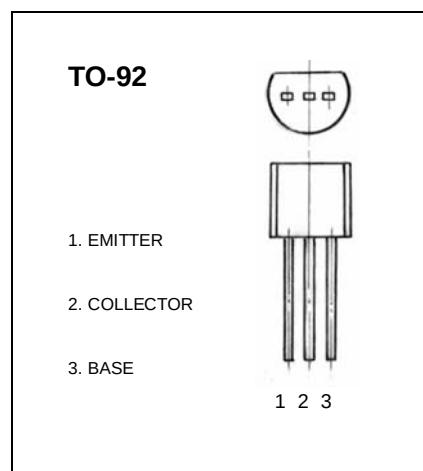
Collector current

 I_{CM} : -100 mA

Collector-base voltage

 $V_{(BR)CBO}$: BF421 -300 V
BF423 -250 V

Operating and storage junction temperature range

 T_J, T_{stg} : -55 to +150**ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage BF421 BF423	V_{CBO}	$I_C=-100\mu A, I_E=0$	-300 -250			V
Collector-emitter breakdown voltage BF421 BF423	V_{CEO}	$I_C=-1mA, I_B=0$	-300 -250			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-200V, I_E=0$			-0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.05	μA
DC current gain	h_{FE}	$V_{CE}=-20V, I_C=-25mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-30mA, I_B=-5mA$			-0.6	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-10mA$	60			MHz